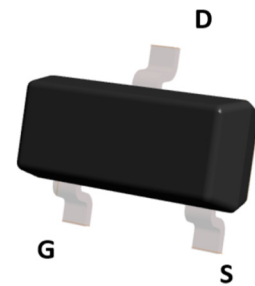
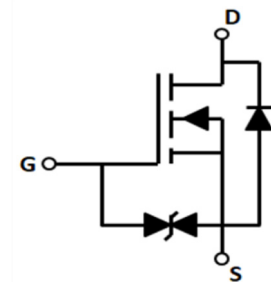
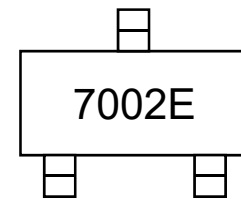


Description

The MOSFET provide the best combination of fast switching , low on-resistance and cost-effectiveness.

- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- Low input Capacitance
- Fast Switching Speed
- Low Input / Output Leakage


Top View

Circuit Diagram

Marking (Top View)

| MOSFET Product Summary | | |
|------------------------|----------------------|----------|
| $V_{DS}(V)$ | $R_{DS(on)}(\Omega)$ | $I_D(A)$ |
| 60 | 4@ $V_{GS} = 10V$ | 0.34 |
| | 5@ $V_{GS} = 5V$ | |

Applications

- Battery operated systems
- Solid-state relays
- Direct logic-level interface: TTL/CMOS

Absolute maximum rating@25°C

| Rating | Symbol | Value | Units |
|---------------------------------------------------------------------|-----------------|----------|--------------|
| Drain-source Voltage | V_{DS} | 60 | V |
| Gate-source Voltage | V_{GS} | ± 20 | V |
| Drain Current | I_D | 115 | mA |
| Pulsed Drain Current ¹⁾ | I_{DM} | 1.5 | A |
| Total Power Dissipation @ $T_A=25^\circ C$ | P_D | 200 | mW |
| Thermal Resistance Junction-to-Ambient @ Steady State ²⁾ | $R_{\theta JA}$ | 215 | $^\circ C/W$ |
| Junction and Storage Temperature Range | T_J, T_{STG} | -55~+150 | $^\circ C$ |

Notes:

1) Pulse Test: Pulse Width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2) Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

Electrical characteristics per line@25°C (unless otherwise specified)

| Parameter | Symbol | Conditions | Min. | Typ. | Max. | Units |
|---------------------------------------|--------------|-------------------------------------------------------------------|------|------|---------|----------|
| Static Parameter | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS} = 0V, I_D = 250\mu A$ | 60 | - | - | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 60V, V_{GS} = 0V$ | - | - | 1 | μA |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS} = \pm 20V, V_{DS} = 0V$ | - | - | ± 1 | μA |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\mu A$ | 1 | - | 2.5 | V |
| Static Drain-Source On-Resistance | $R_{DS(on)}$ | $V_{GS} = 10V, I_D = 500mA$ | - | 3.3 | 4.0 | Ω |
| | | $V_{GS} = 5.0V, I_D = 50mA$ | - | 3.5 | 5.0 | |
| Diode Forward Voltage | V_{SD} | $I_S = 250mA, V_{GS} = 0V$ | - | - | 1.0 | V |
| Maximum Body-Diode Continuous Current | I_S | | - | - | 340 | mA |
| Dynamic Parameters | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS} = 30V, V_{GS} = 0V,$ $f = 1MHz$ | - | 18 | - | pF |
| Output Capacitance | C_{oss} | | - | 12 | - | |
| Reverse Transfer Capacitance | C_{rss} | | - | 7 | - | |
| Switching Parameters | | | | | | |
| Total Gate Charge | Q_g | $V_{GS} = 10V, V_{DS} = 30V,$ $I_D = 0.3A$ | - | 1.7 | 2.4 | nC |
| Turn-on Delay Time | $t_{D(on)}$ | $V_{GS} = 10V, V_{DD} = 30V,$ $I_D = 300mA, R_{GEN} = 6\Omega$ | - | 5 | - | ns |
| Turn-off Delay Time | $t_{D(off)}$ | | - | 17 | - | |
| Reverse recovery Time | t_{rr} | $V_{GS} = 0V, I_S = 300mA,$ $V_R = 25V, dI_S/dt = -100A/\mu s$ | - | 30 | - | ns |

Typical Characteristics

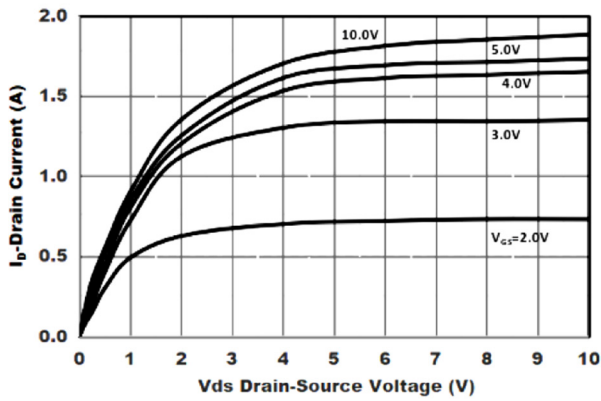


Figure1. Output Characteristics

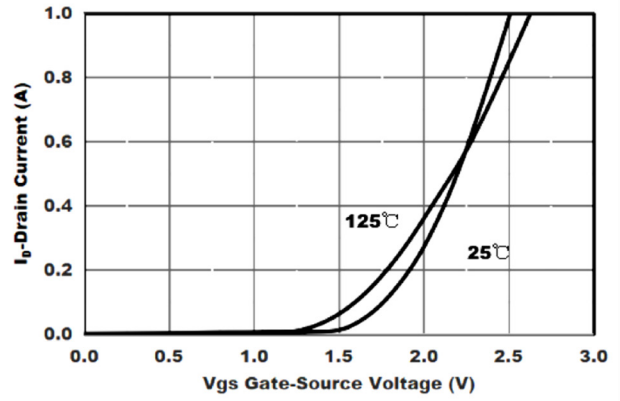


Figure2. Transfer Characteristics

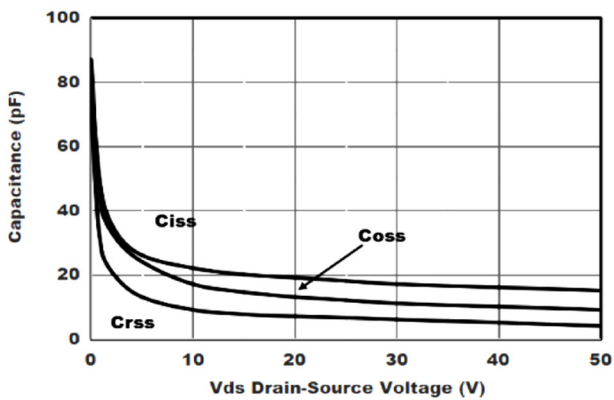


Figure3. Capacitance Characteristics

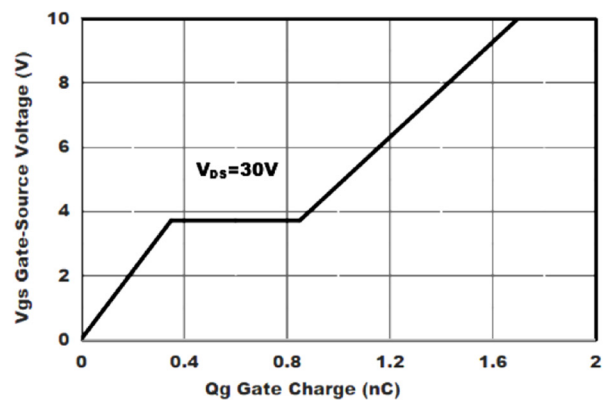


Figure4. Gate Charge

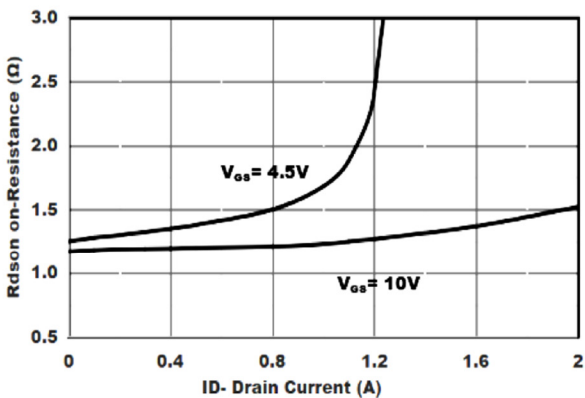


Figure5. Drain-Source on Resistance

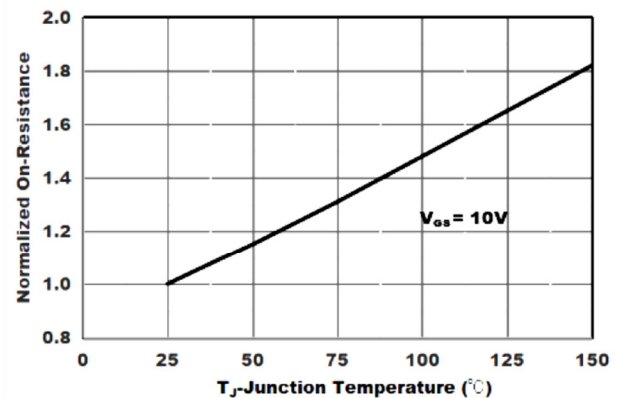


Figure6. Drain-Source on Resistance

N-Channel MOSFET

PNMT7002E

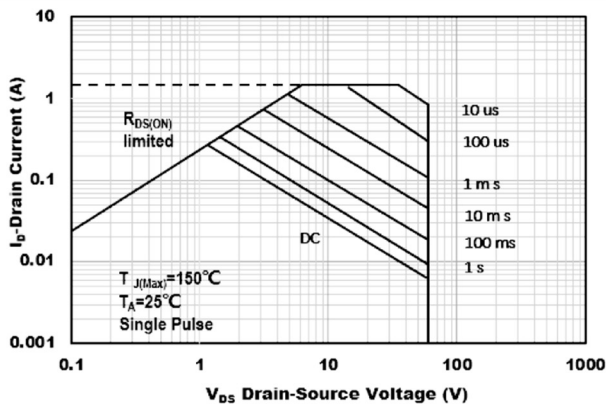


Figure7. Safe Operation Area

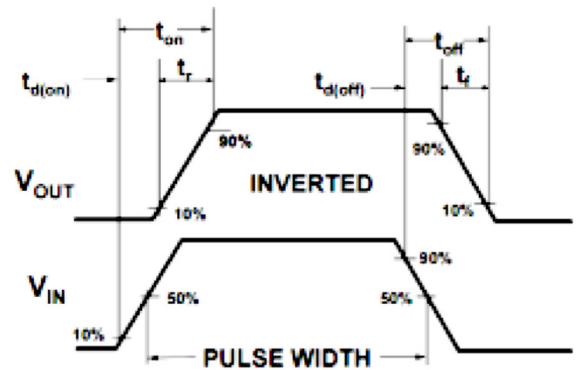
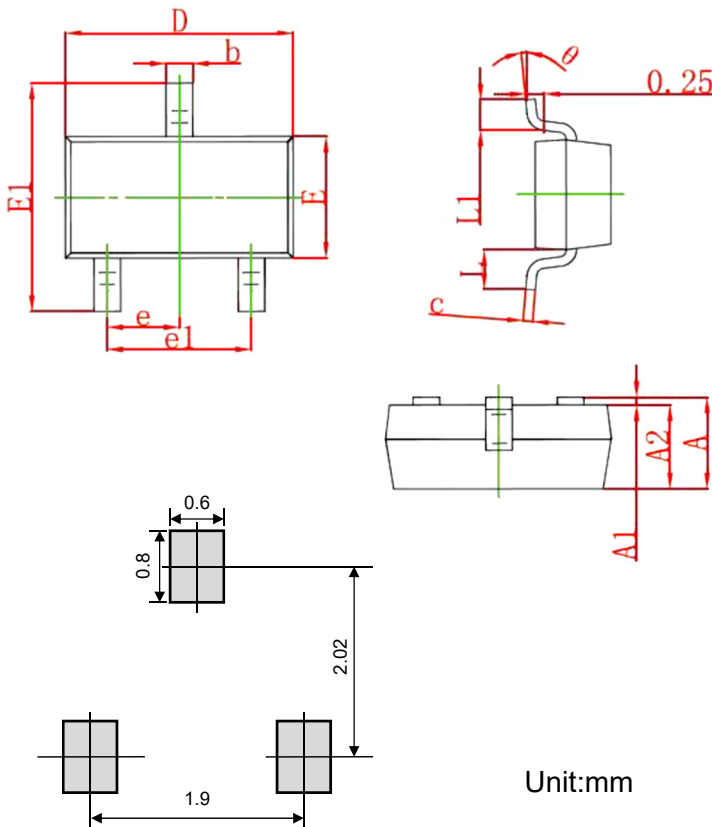


Figure8. Switching wave

Product dimension (SOT-23)




| Dim | Millimeters | | Inches | |
|-----|-------------|-------|------------|-------|
| | Min | Max | Min | Max |
| A | 0.900 | 1.150 | 0.035 | 0.045 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 0.900 | 1.050 | 0.035 | 0.041 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.080 | 0.150 | 0.003 | 0.006 |
| D | 2.800 | 3.000 | 0.110 | 0.118 |
| E | 1.200 | 1.400 | 0.047 | 0.055 |
| E1 | 2.250 | 2.550 | 0.089 | 0.100 |
| e | 0.950 Typ. | | 0.037 Typ. | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.550 Ref. | | 0.022 Ref. | |
| L1 | 0.300 | 0.500 | 0.012 | 0.020 |
| θ | 0° | 8° | 0° | 8° |

Suggested PCB Layout

Ordering information

| Device | Package | Reel | Shipping |
|-----------|------------------|------|--------------------|
| PNMT7002E | SOT-23 (Pb-Free) | 7" | 3000 / Tape & Reel |


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